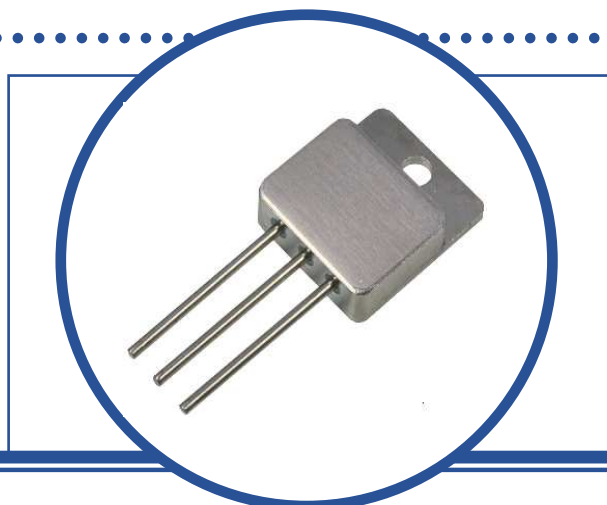


SILICON CARBIDE POWER SCHOTTKY RECTIFIER DIODE

SML020DH12

- 1200V, 20A (2x10A) Rectifier Diodes
- High Temperature Operation $T_j = 200^\circ\text{C}$
- Effective Zero Reverse and Forward Recovery
- High Frequency Operation
- High Speed Low Loss Switching



ABSOLUTE MAXIMUM RATINGS ($T_c = 25^\circ\text{C}$ unless otherwise stated)

V_{RRM}	Repetitive Peak Reverse Breakdown Voltage	1200V
V_{RSM}	Surge Peak Reverse Voltage	1200V
V_{DC}	DC Blocking Voltage	1200V
$I_{F(AVG)}$	Average Forward Current	20A
$I_{F(PEAK)}$	Peak Forward Surge Current, $T_c = 125^\circ\text{C}$	50A
P_D	Power Dissipation (per leg)	116W
T_j	Junction Temperature Range	-55 to +200°C
T_{stg}	Storage Temperature Range	-55 to +225°C

THERMAL PROPERTIES

Symbols	Parameters	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction To Case	1.5	°C/W

ELECTRICAL CHARACTERISTICS (Per Die, $T_c = 25^\circ\text{C}$ unless otherwise stated)

Symbols	Parameters	Test Conditions	Min.	Typ.	Max.	Units
$V_F^{(1)}$	Forward Voltage	$I_F = 10\text{A}$ $T_c = 175^\circ\text{C}$		1.6	1.8	V
				2.5	3.0	
I_R	Reverse Current	$V_R = V_{RRM}$ $T_c = 175^\circ\text{C}$		10	200	μA
				20	1000	

DYNAMIC CHARACTERISTICS ($T_c = 25^\circ\text{C}$ unless otherwise stated)

$Q_C^{(2)}$	Total Capacitive Charge	$I_F = 10\text{A}$ $di/dt = 500\text{A}/\mu\text{s}$	$V_R = 1200\text{V}$ $T_j = 25^\circ\text{C}$		61		nC
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Notes

- (1) Pulse Width $\leq 380\mu\text{s}$, $\delta \leq 2\%$
 (2) By Design. Not a production test.

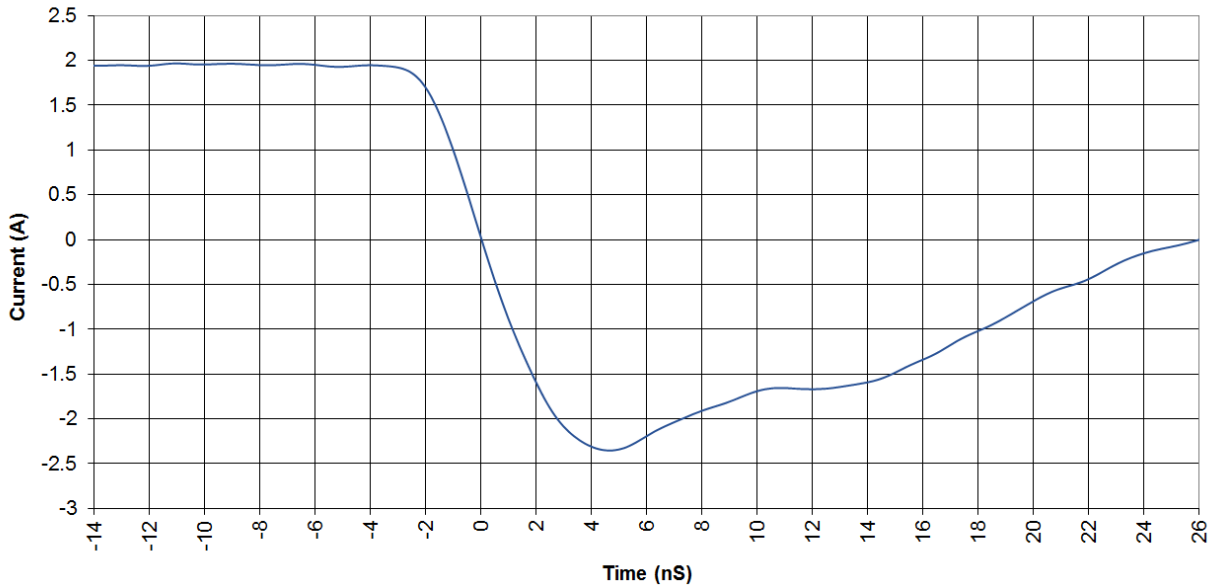
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SILICON CARBIDE POWER SCHOTTKY RECTIFIER DIODE SML020DH12

Equivalent Reverse Recovery Time ⁽³⁾

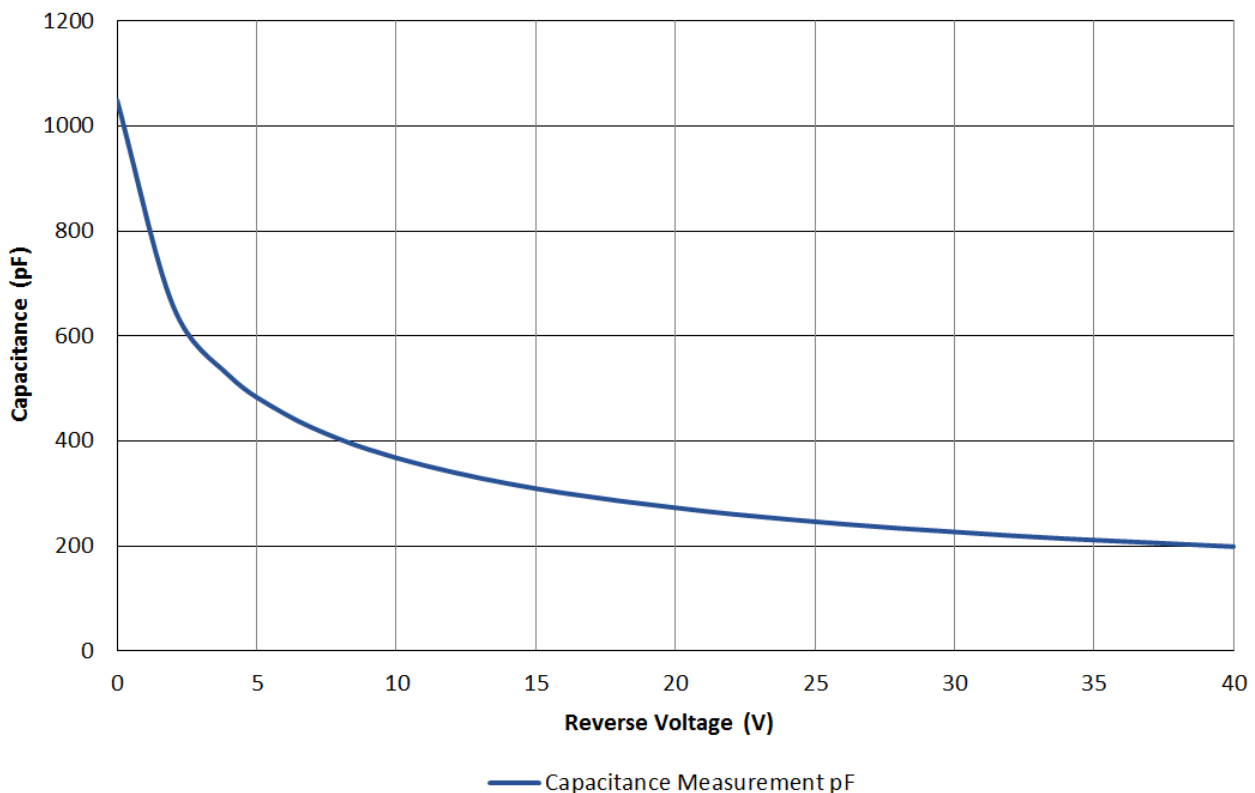
$I_F=2A, V_R = 140V, I_{RR}=250mA$



Notes

- (3) SiC Schottky Diode, no minority carrier recombination thus zero reverse recovery. Recovery time shown is due to a small junction capacitance charge and is independent of junction temperature

Capacitance vs Reverse Voltage

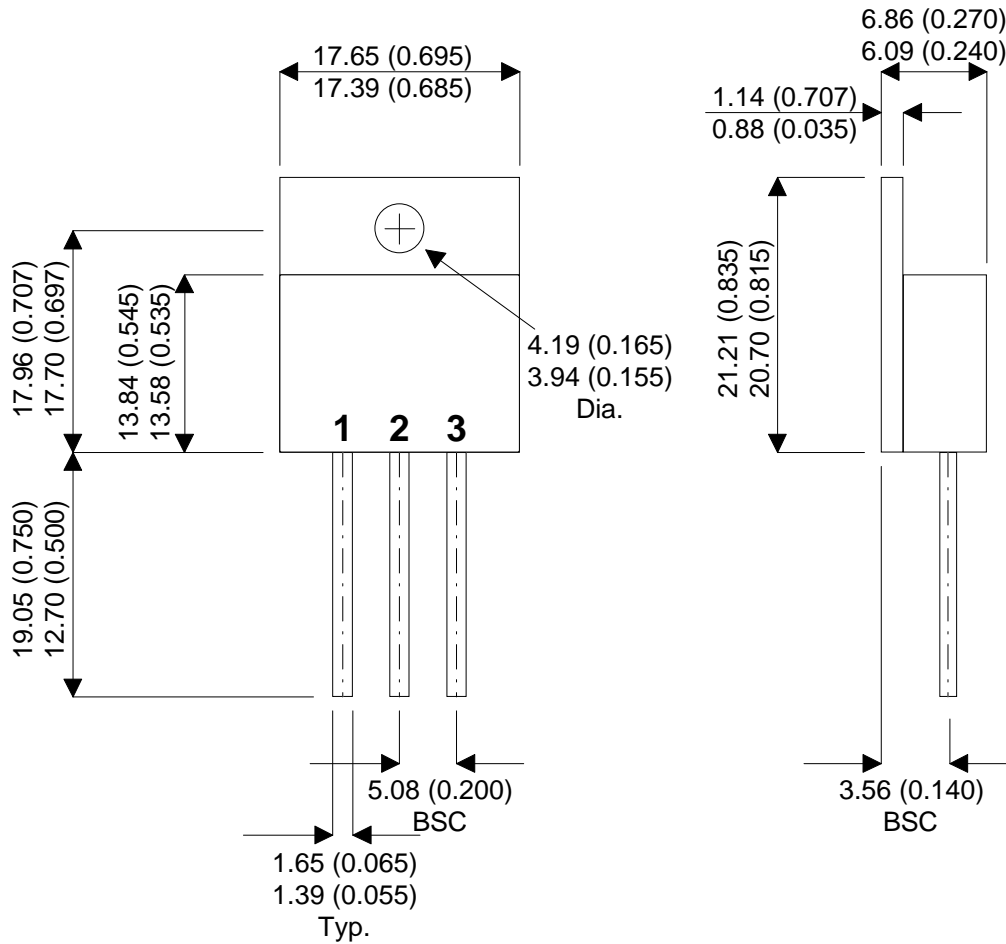


SILICON CARBIDE POWER SCHOTTKY RECTIFIER DIODE

SML020DH12

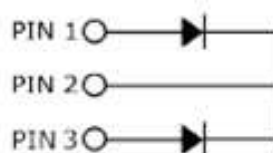
MECHANICAL DATA

Dimensions in mm (Inches)



TO258 (TO-258AA)

Pin 1 – Anode Pin 2 - Cathode Pin 3 – Anode



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